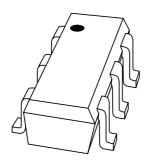
# **DISCRETE SEMICONDUCTORS**

# DATA SHEET



# **BAT754L**Schottky barrier triple diode

Product data sheet 2001 Jan 18



# Schottky barrier triple diode

### BAT754L

#### **FEATURES**

- · Very low forward voltage
- · Guard ring protected
- · Low diode capacitance
- Three independent diodes in a small plastic SMD package.

#### **APPLICATIONS**

- · Ultra high-speed switching
- Voltage clamping
- · Protection circuits
- · Blocking diodes
- Low power consumption applications (e.g. hand-held applications).

#### **DESCRIPTION**

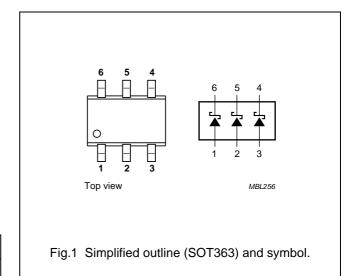
Three internal (galvanic) isolated silicon epitaxial Schottky barrier diodes in a SOT363 small SMD plastic package.

#### **MARKING**

TYPE NUMBER	MARKING CODE
BAT754L	L1

#### **PINNING**

PIN	DESCRIPTION			
1	anode 1			
2	anode 2			
3	anode 3			
4	cathode 3			
5	cathode 2			
6	cathode 1			



#### **LIMITING VALUES**

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	PARAMETER CONDITIONS		MAX.	UNIT
Per diode					
V <sub>R</sub>	continuous reverse voltage		_	30	V
I <sub>F</sub>	continuous forward current		-	200	mA
I <sub>FRM</sub>	repetitive peak forward current	$t_p < 1 \text{ s}; \delta < 0.5$	_	300	mA
I <sub>FSM</sub>	non-repetitive peak forward current	t <sub>p</sub> < 10 ms	_	600	mA
T <sub>stg</sub>	storage temperature		-65	+150	°C
Tj	junction temperature		_	125	°C
T <sub>amb</sub>	operating ambient temperature		-65	+125	°C

# Schottky barrier triple diode

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#### THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R <sub>th j-a</sub>	thermal resistance from junction to ambient	note 1	416	K/W

#### Note

1. Refer to SOT363 standard mounting conditions.

#### **ELECTRICAL CHARACTERISTICS**

 $T_{amb}$  = 25 °C; unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MAX.	UNIT
Per diode				
V <sub>F</sub>	forward voltage	note 1; see Fig.2		
		$I_F = 0.1 \text{ mA}$	200	mV
		I <sub>F</sub> = 1 mA	260	mV
		I <sub>F</sub> = 10 mA	340	mV
		I <sub>F</sub> = 30 mA	420	mV
		I <sub>F</sub> = 100 mA	750	mV
I <sub>R</sub>	reverse current	V <sub>R</sub> = 25 V; note 1; see Fig.3	2	μΑ
C <sub>d</sub>	diode capacitance	V <sub>R</sub> = 1 V; f = 1 MHz; see Fig.4	10	pF

#### Note

1. Pulse test: pulse width = 300  $\mu$ s;  $\delta$  = 0.02.

# Schottky barrier triple diode

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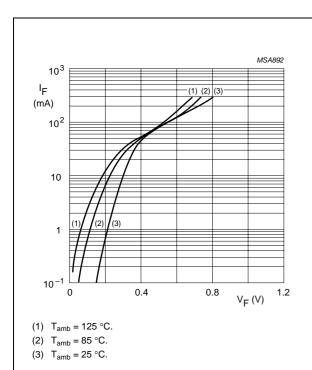
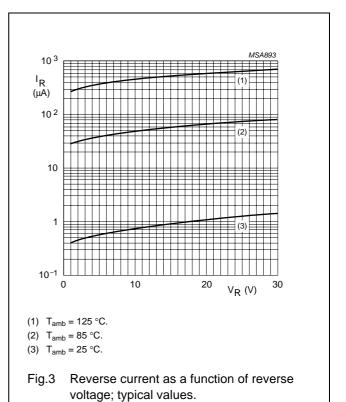
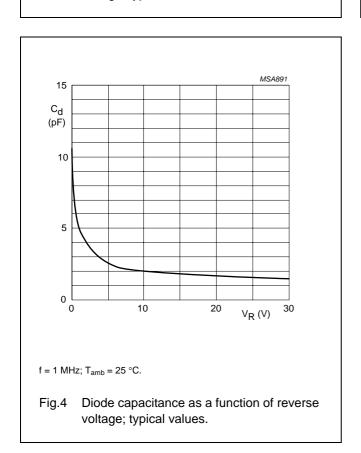


Fig.2 Forward current as a function of forward voltage; typical values.





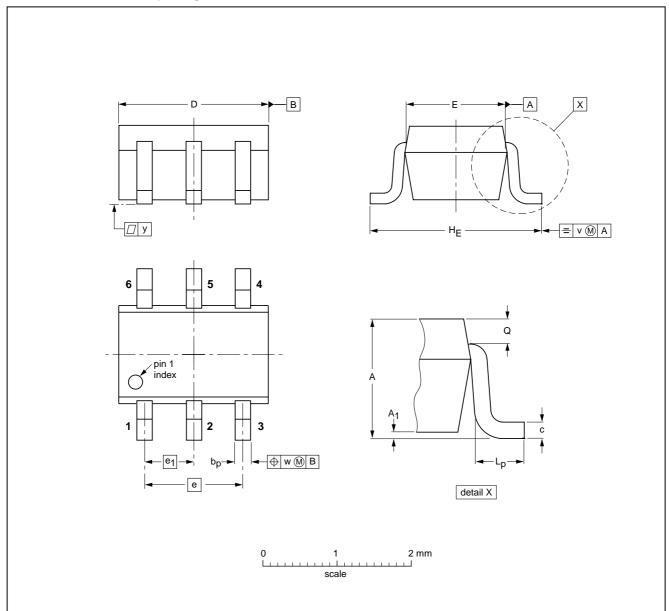
# Schottky barrier triple diode

BAT754L

#### **PACKAGE OUTLINE**

#### Plastic surface mounted package; 6 leads

SOT363



#### **DIMENSIONS** (mm are the original dimensions)

UNIT	A	A <sub>1</sub> max	bp	С	D	E	е	e <sub>1</sub>	HE	Lp	ø	v	w	у
mm	1.1 0.8	0.1	0.30 0.20	0.25 0.10	2.2 1.8	1.35 1.15	1.3	0.65	2.2 2.0	0.45 0.15	0.25 0.15	0.2	0.2	0.1

OUTLINE		REFERENCES				ISSUE DATE	
VERSION	IEC	JEDEC EIAJ			PROJECTION	ISSUE DATE	
SOT363			SC-88		$ \  \   \bigoplus   \big($	97-02-28	

## Schottky barrier triple diode

BAT754L

#### **DATA SHEET STATUS**

DOCUMENT STATUS <sup>(1)</sup>	PRODUCT STATUS <sup>(2)</sup>	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

#### **Notes**

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- 2. The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

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#### **Contact information**

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